

RECEIVED
CENTRAL FAX CENTER

FEB 04 2008

Amendment to the Specification:

This listing of specification will replace all prior versions of the corresponding paragraphs of specification in the application.

Listing of Amended Paragraphs of Specification:

Please amend the paragraph beginning on page 25, line 22 to read as follows:

As a gas used in an atmosphere for sputtering in forming the crystalline nucleation layer 109, Ar gas, Kr gas, a mixture of Ar gas and a reactive gas, or a mixture of Kr gas and a reactive gas, for example, can be used. Further, the crystalline nucleation layer 109 also can be formed by simultaneously performing sputtering, using a plurality of power sources, with respect to respective sputtering targets of Bi, Te, and M1. Further, the crystalline nucleation layer 109 also can be formed by simultaneously performing sputtering, using a plurality of power sources, with respect to a binary sputtering target, a ternary sputtering target, or the like in which any of Bi, Te, and M1 are combined. In each of these cases where such sputtering targets are used, the crystalline nucleation layer 109 also can be formed by performing sputtering in an atmosphere of Ar gas, Kr gas, a mixture of Ar gas and a reactive gas, or a mixture of Kr gas and a reactive gas.

Please amend the paragraph beginning on page 81, line 17 to read as follows:

As shown in Table 6, with respect to each of Samples 14-a to 14-f, the difference between before and after sample storage in the high-temperature environment was within 2%, and excellent archival characteristics were exhibited. On the other hand, with respect to the archival overwrite characteristics, only Samples 14-a to 14-e in each of which the crystalline nucleation layer 503 was formed of a material made of Bi and the element M1 exhibited excellent results with a difference in jitter of within 2%. With respect to Sample 14-f in which SnTe was used, it was confirmed that the difference in

jitter was large at 5.1% and excellent archival overwrite characteristics were not obtained.

As described above, it was confirmed that in the case where the crystalline nucleation layer 503 was made of a material made of ~~B1~~Bi and the element M1, both excellent archival characteristics in the case of a linear velocity of 8.2 m/s (low velocity) and excellent archival overwrite characteristics in the case of a linear velocity of 20.5 m/s (high velocity) were obtained.